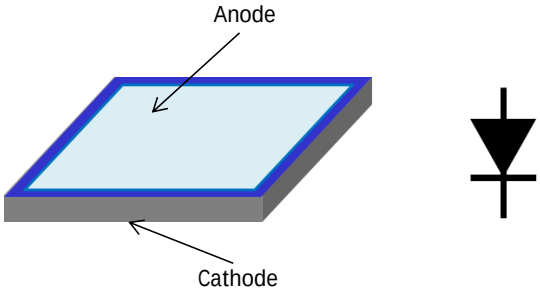
YJ Planar Schottky Barrier Diode Die Specification

40V 0.04A,9mil, Schottky barrier diode die based on silicon planar process
Part No.: PSB009L040AG-155A

Main Products Characterstics



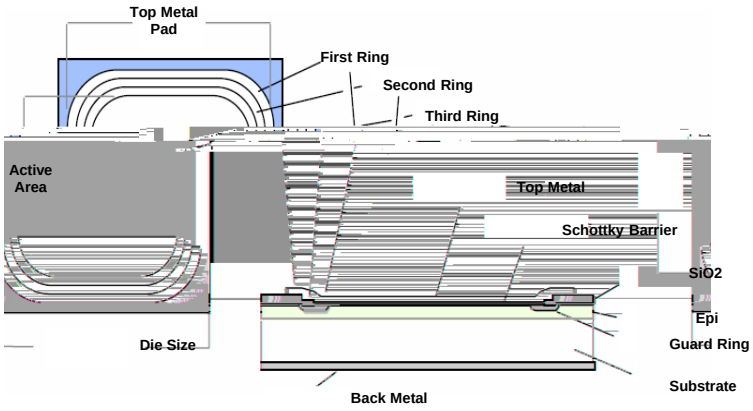
Maximum Ratings

Parameter	Symbol	Rating
Repetitive peak reverse voltage	V_{RRM}	40 V
Average forward current	$I_{F(AV)}$	0.04A
current (tp = 8.3 ms, halfwave, 1 cycle)	I_{FSM}	1 A
Storage temperature range	T_{stg}	-50 to +125 °C
Maximum operating junction temperature	T_j	125 °C

Static Electrical Characteristics (Ta = 25°C)

Parameter	Symbol	Value	
		Spec	Typical
Reverse breakdown voltage I_R = 100uA	V_{BR}	45 V	52V
Maximum forward voltage drop I_F =0.04A 2%	V_F	1V	0.63V
Maximum reverse current V_R = 40V 2%	I_R	0.5uA	0.07uA

Device Schematics and Outline Drawing



Die Thickness *	155um
Die Size **	230um
Top Metal Pad	170um
Active Area	100um
Top Metal	AL/3.915um
Back Metal	Au/1.2um
Steet width	60um

Important Notice

Specification apply to die only. Actual performance may degrade when assembled.

Yangjie Electronics does not guarantee device performance after assembly.
All operating parameters must be validated for each customer application by customer's technical experts.

Data sheet information is subjected to change without notice.

Recommended Storage Environment:

Store in original container, in dessicated nitrogen, with no contamination.

Shelf life for parts stored in above condition is 2 years.

If the storage is done in normal atmosphere shelf life is reduced to 6 months.